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Record Nr.	UNINA9910784537803321
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Titolo	Dilute nitride semiconductors [[electronic resource] /] / [edited by] M. Henini
Pubbl/distr/stampa	Amsterdam, : Elsevier, 2005
ISBN	1-280-62834-0 9786610628346 0-08-045599-9
Edizione	[1st ed.]
Descrizione fisica	1 online resource (648 p.)
Disciplina	621.38152 621.3'8152
Soggetti	Semiconductors Nitrides
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Cover; Frontmatter; Half Title Page; Copyright; Title Page; Copyright; Preface; Contents; 1. MBE Growth and Characterization of Long Wavelength Dilute Nitride III-V Alloys; 1.1. INTRODUCTION; 1.3. DILUTE NITRIDE CHARACTERIZATION; 1.4. ENERGY BAND AND CARRIER TRANSPORT PROPERTIES; 1.6. SUMMARY; ACKNOWLEDGEMENTS; REFERENCES; 2. Epitaxial Growth of Dilute Nitrides by Metal-Organic Vapour Phase Epitaxy; 2.1. INTRODUCTION; 2.2. EPITAXIAL GROWTH OF GaInAsN-BASED STRUCTURES; 2.3. LONG WAVELENGTH GaAs-BASED LASER PERFORMANCES; 2.4. CONCLUSION; ACKNOWLEDGEMENTS; REFERENCES 3. The Chemical Beam Epitaxy of Dilute Nitride Alloy Semiconductors3. 1. INTRODUCTION TO DILUTE NITRIDE SEMICONDUCTORS; 3.2. THE CHEMICAL BEAM EPITAXIAL/METALORGANIC MOLECULAR BEAM EPITAXIAL (CBE/MOMBE) GROWTH PROCESS; 3.3. CBE OF DILUTE NITRIDE SEMICONDUCTORS; 3.4. FUNDAMENTAL STUDIES OF GaNxAs (1-x) BAND STRUCTURE; 3.5. THE COMPOSITIONS AND PROPERTIES OF DILUTE NITRIDES GROWN BY CBE; 3.6. CBE-GROWN DILUTE NITRIDE DEVICES; 3.7. THE POTENTIAL FOR PRODUCTION CBE OF DILUTE NITRIDES; 3.8. CONCLUSIONS; ACKNOWLEDGEMENTS; REFERENCES

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Sommario/riassunto

* This book contains full account of the advances made in the dilute nitrides, providing an excellent starting point for workers entering the field. * It gives the reader easier access and better evaluation of future trends, Conveying important results and current ideas * Includes a generous list of references at the end of each chapter, providing a useful reference to the III-V-N based semiconductors research community. The high speed lasers operating at wavelength of 1.3 m and 1.55 m are very important light sources in optical communications since the optical fiber used as a transpo